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(12) **United States Design Patent**
Kondo et al.

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(54) **SEMICONDUCTOR MODULE**

(71) Applicant: **ROHM CO., LTD.**, Kyoto (JP)
(72) Inventors: **Okimoto Kondo**, Kyoto (JP); **Yusuke Nakakohara**, Kyoto (JP)

(73) Assignee: **ROHM CO., LTD.**, Kyoto (JP)

(**) Term: **15 Years**

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(30) **Foreign Application Priority Data**

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(51) **LOC (14) Cl.** **13-03**

(52) **U.S. Cl.**
USPC **D13/182**

(58) **Field of Classification Search**
USPC D13/101, 110, 112, 118, 120, 123, 133,
D13/146, 147, 159, 154, 156, 174, 182,
D13/184, 199; D14/356, 433, 435, 438
CPC H01R 24/00; H01R 12/00; H01R 12/70;
H01R 13/62
See application file for complete search history.

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Primary Examiner — Messina L Smith

Assistant Examiner — Noah Perez

(74) *Attorney, Agent, or Firm* — Hamre, Schumann, Mueller & Larson, P.C.

(57) **CLAIM**

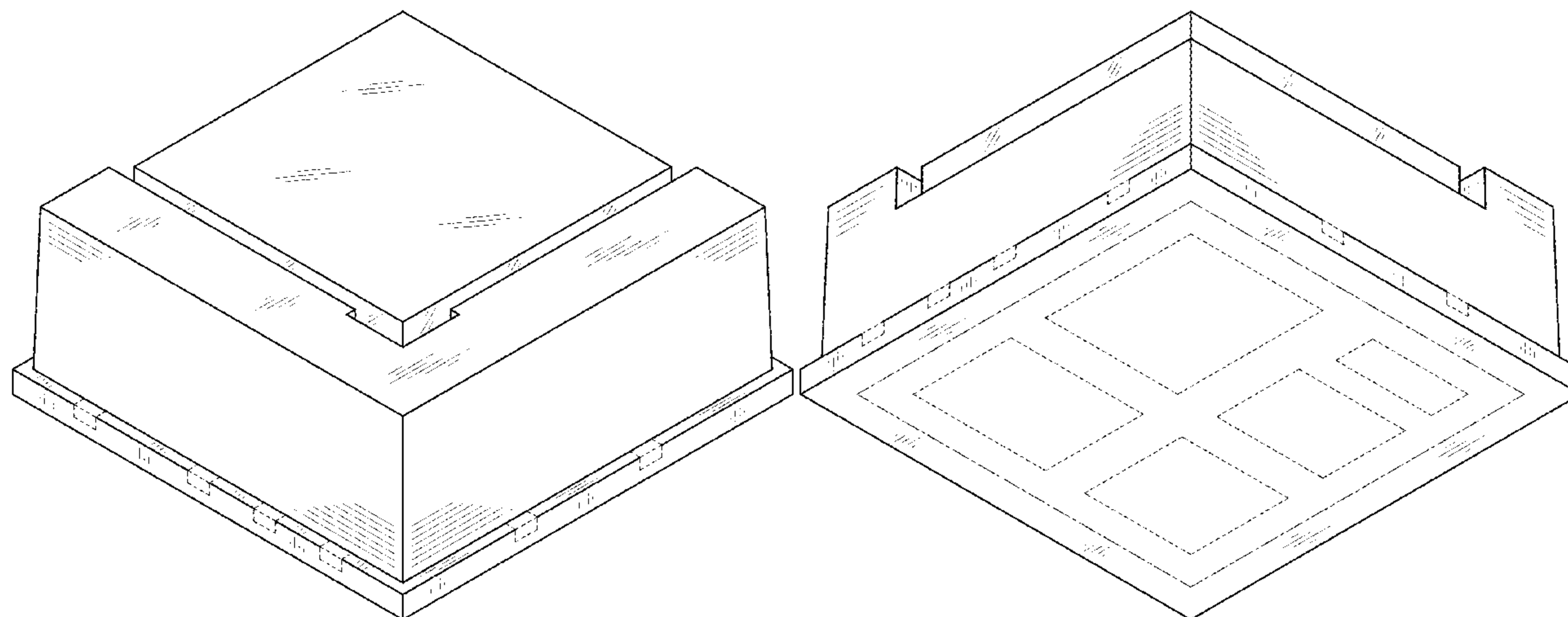
The ornamental design for a semiconductor module, as shown and described.

DESCRIPTION

FIG. 1 is a front, top and right side perspective view of a semiconductor module showing our new design; FIG. 2 is a rear, bottom and left side perspective view thereof; FIG. 3 is a front view thereof; FIG. 4 is a rear view thereof; FIG. 5 is a top plan view thereof; FIG. 6 is a bottom plan view thereof; FIG. 7 is a right side view thereof; and, FIG. 8 is a left side view thereof.

The broken lines illustrate portions of the semiconductor module that form no part of the claimed design. The dash-dotted lines denote the boundary of the claim and form no part of the claimed design. The member illustrated with fine, diagonal, parallel lines is translucent.

1 Claim, 8 Drawing Sheets



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FIG. 1

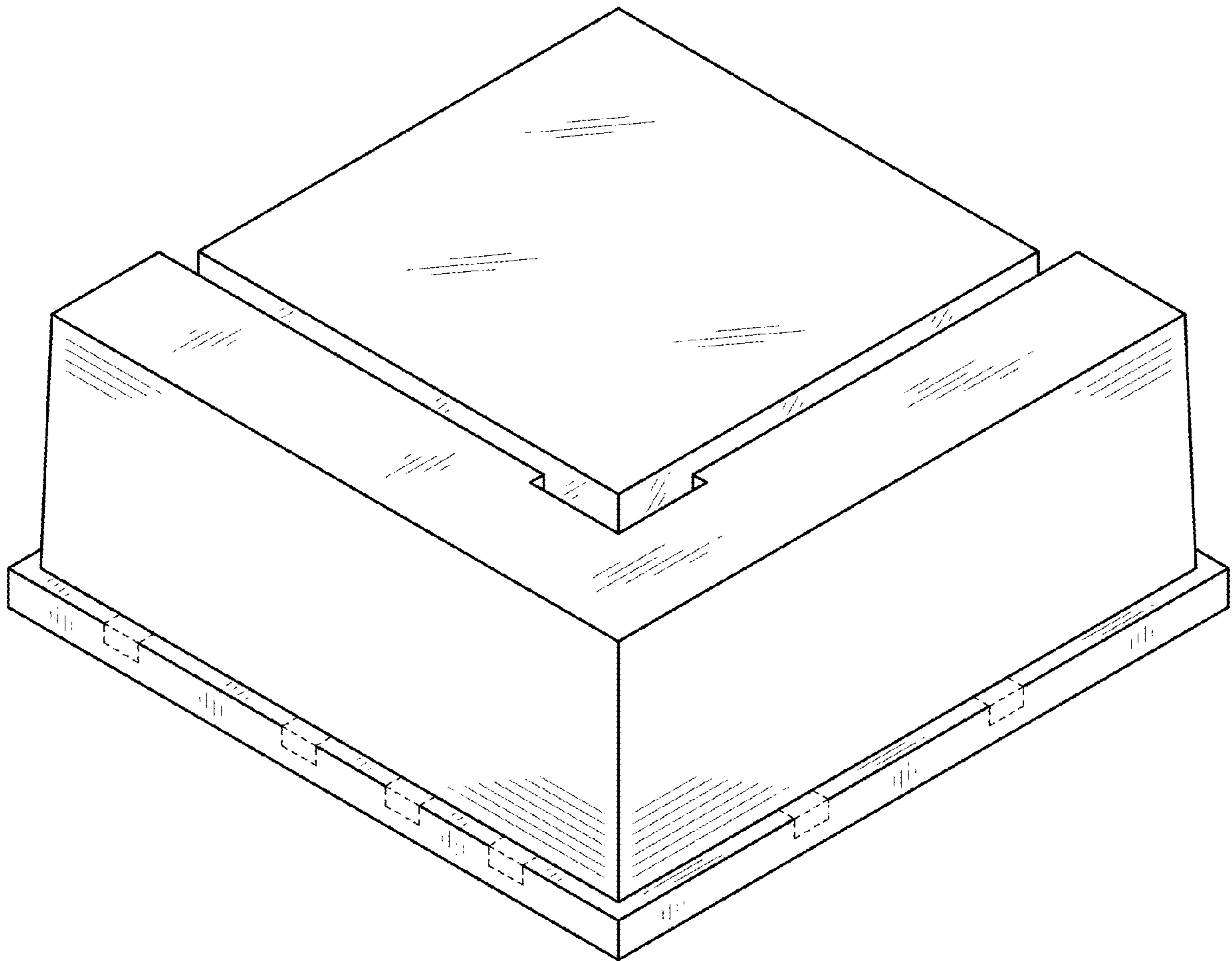


FIG.2

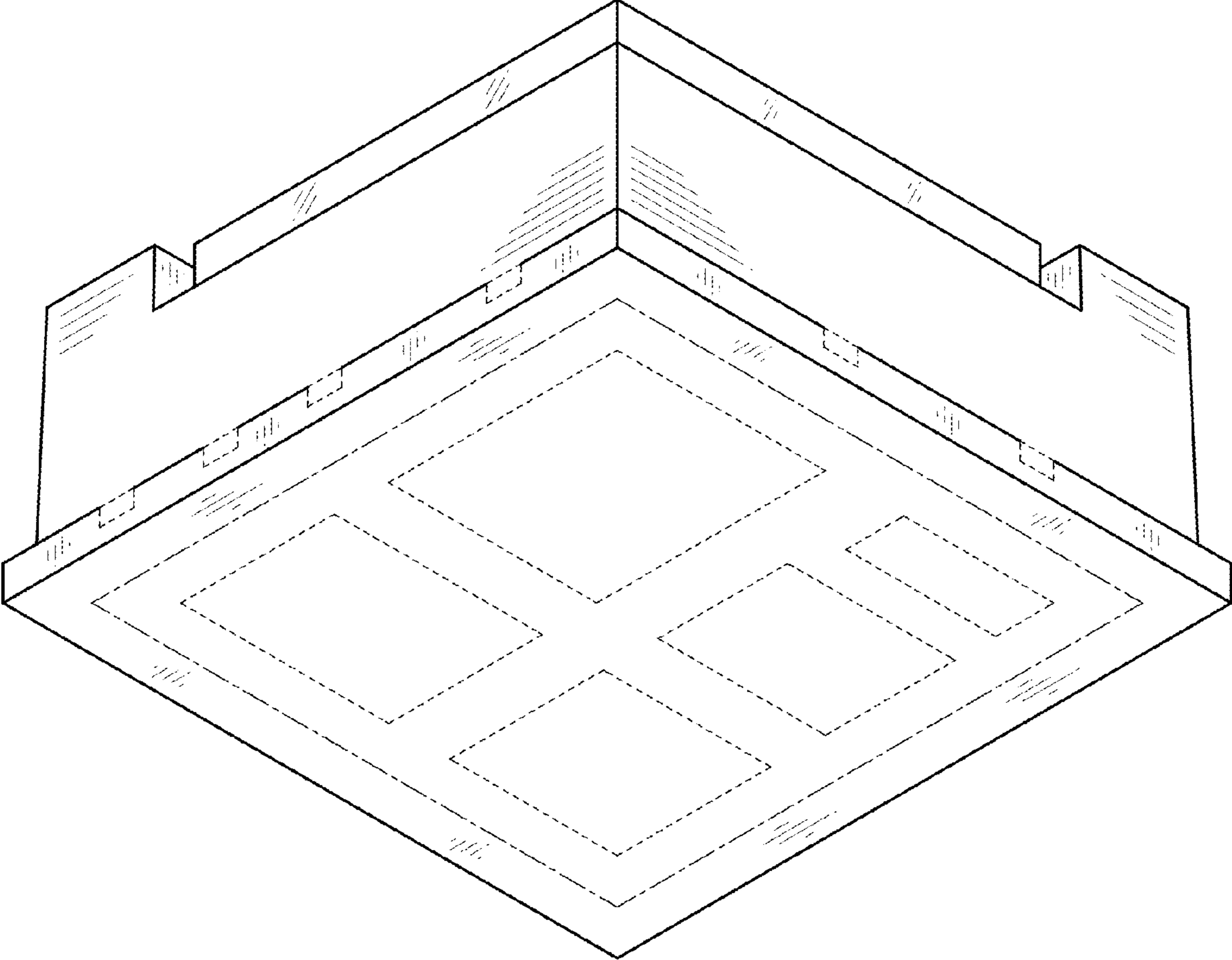


FIG.3

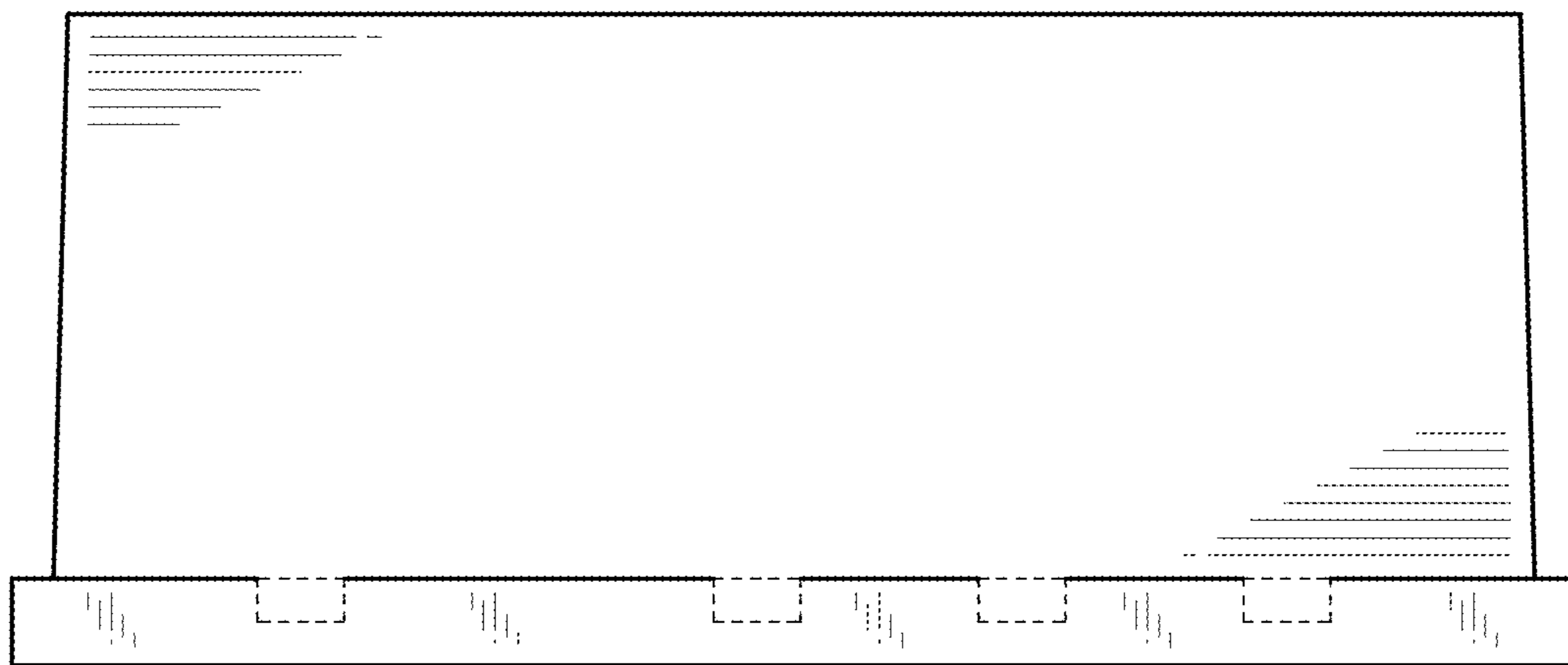


FIG.4

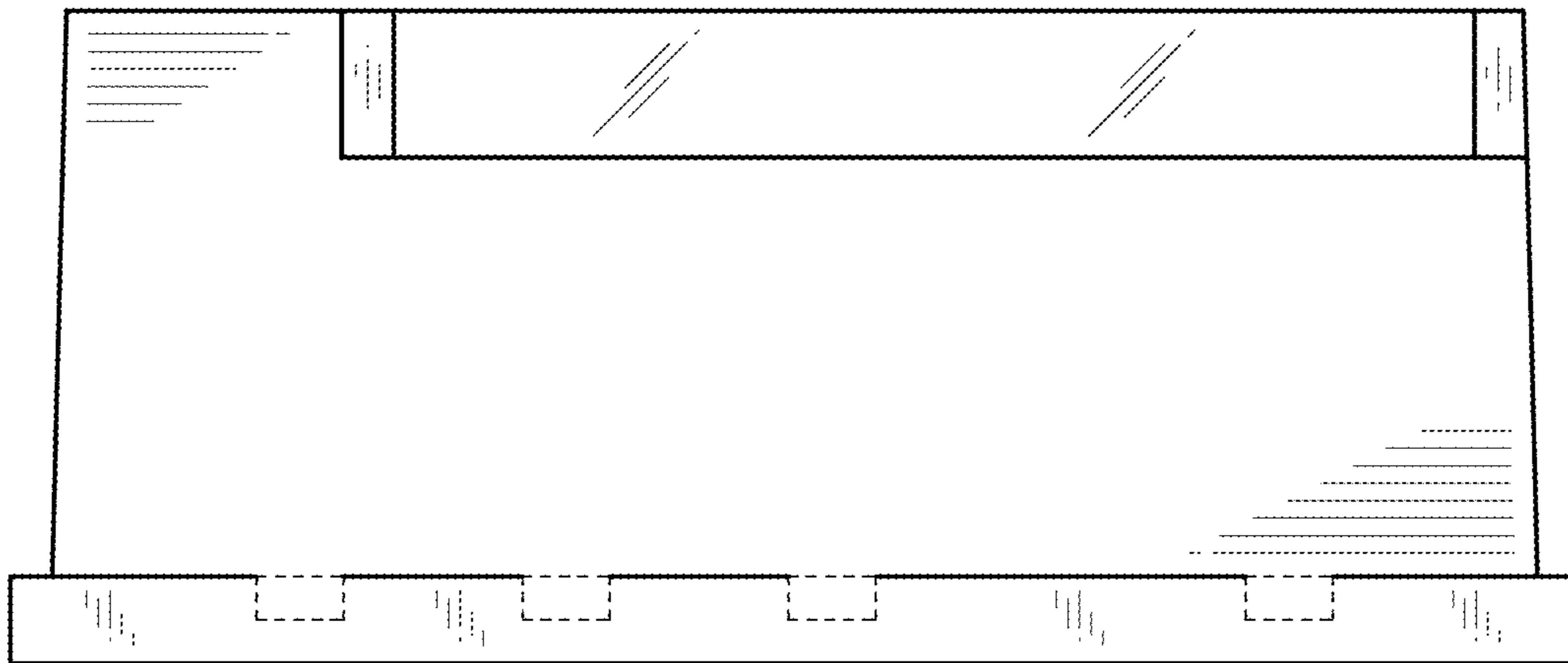


FIG.5

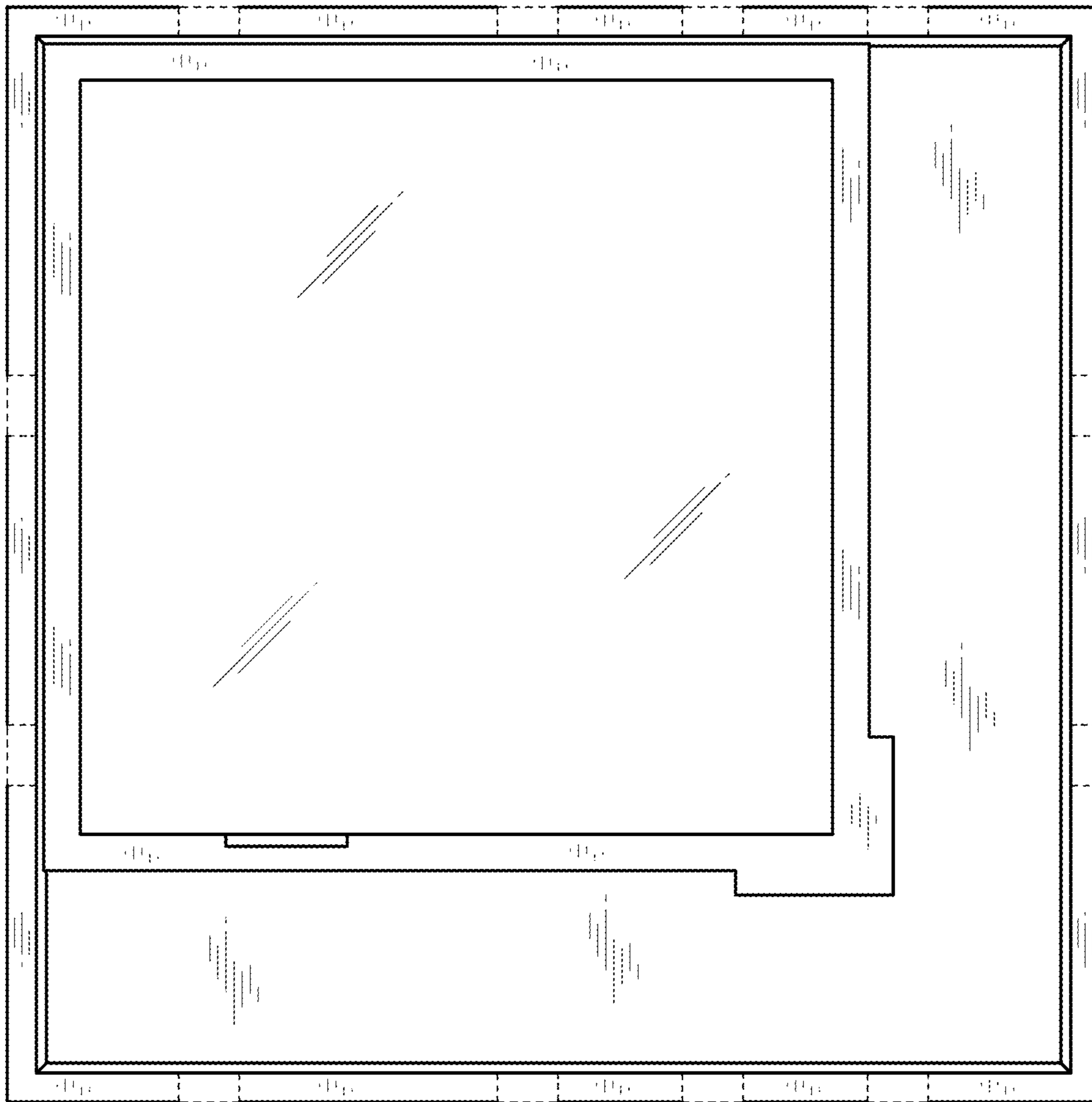


FIG.6

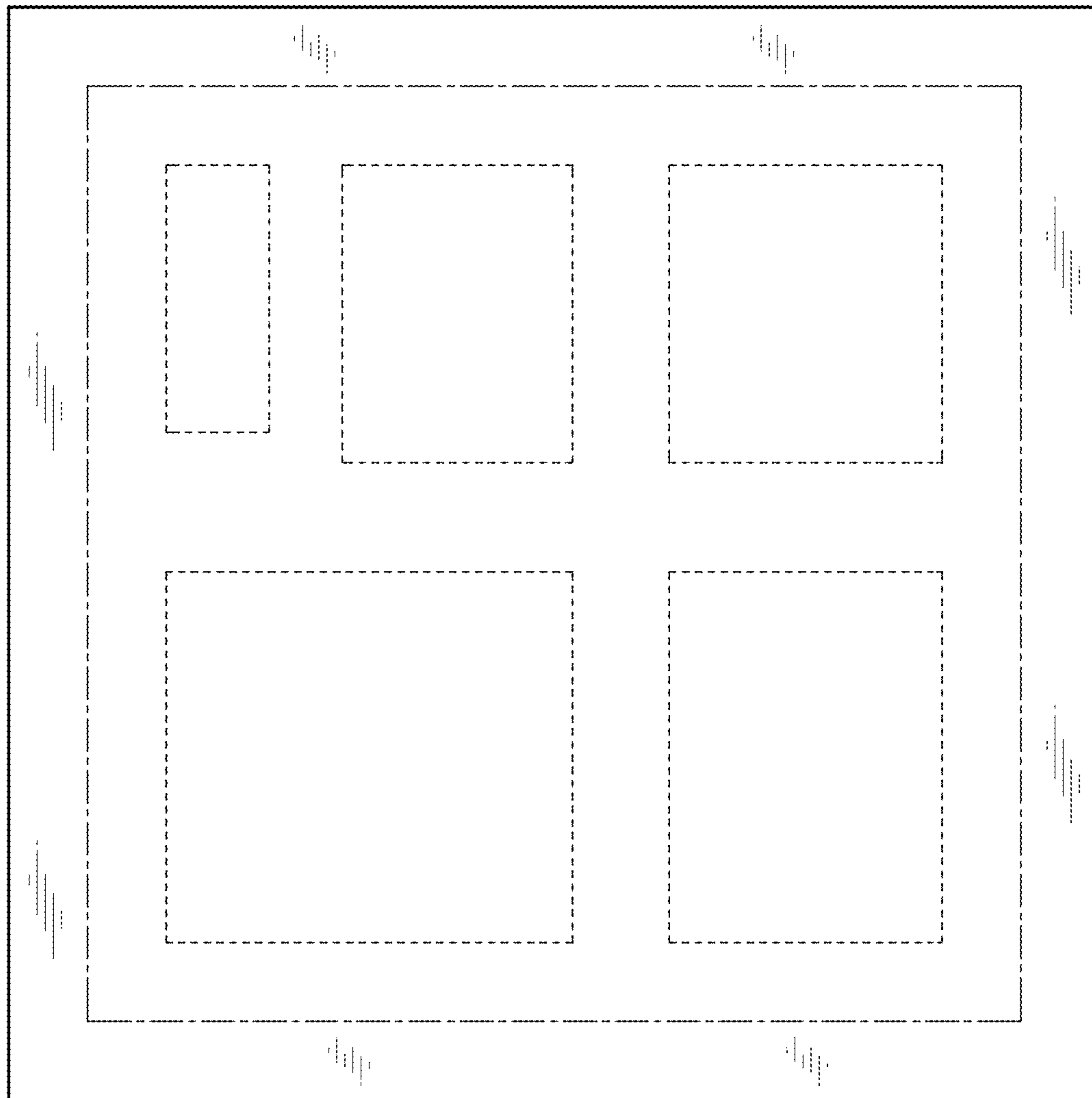


FIG.7

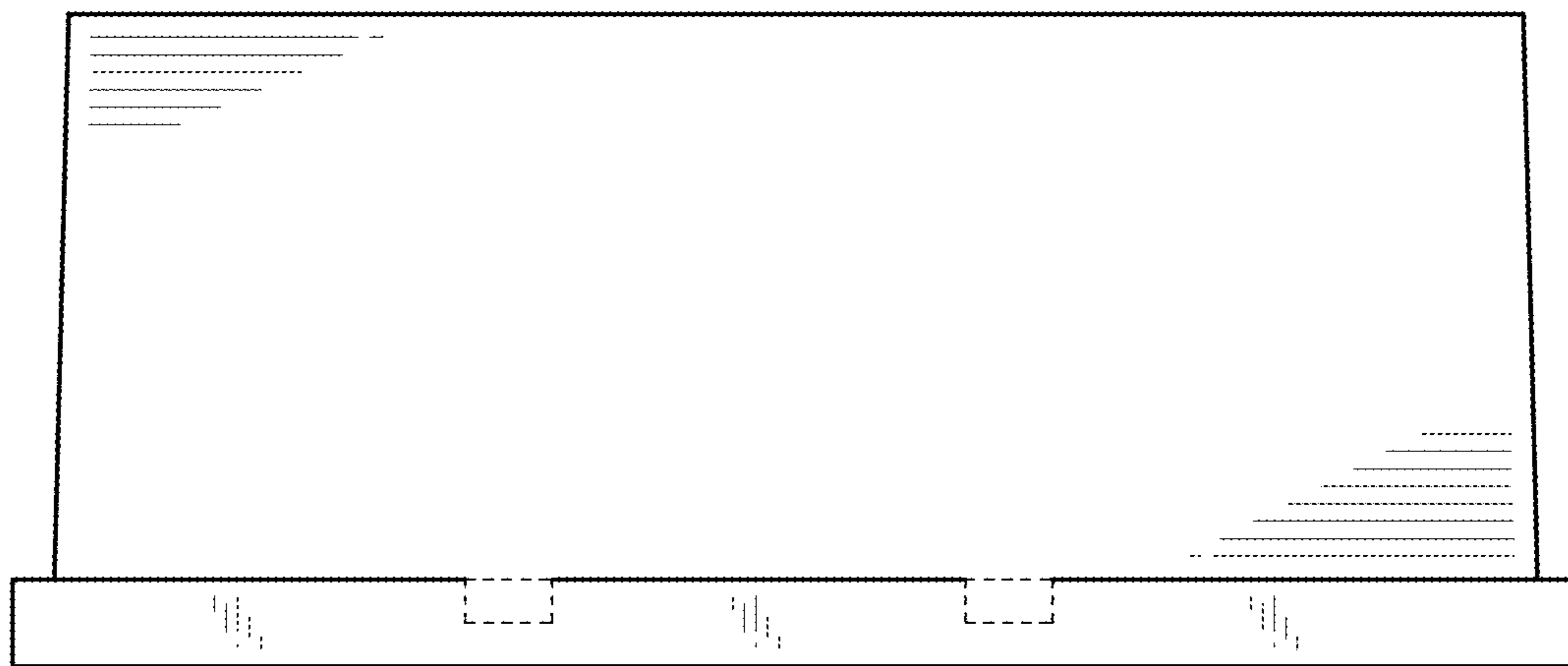


FIG.8

